

SiPM neutron hardening with Cf-252 for space environments

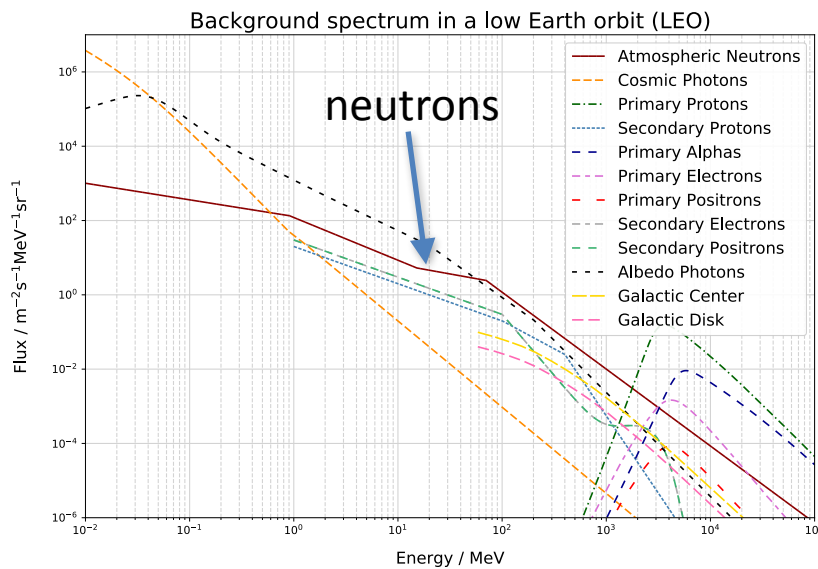
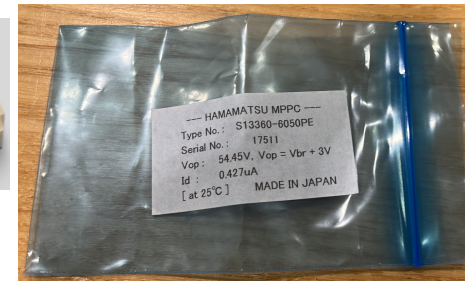
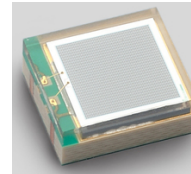
Federico Suarez, Shannon Hoogerheide, Daniel Hussey, Agustín Lucero, Johannes Hulsman

SiPM radiation workshop @ CERN

Geneva, April 26th

Motivation

- Spaceborne instruments are prone to fail with background radiation
- Irradiate with n single SiPM to be used in POLAR-2 polarimeter
 - Hamamatsu S13360-6050PE (6mm x 6mm)
 - Provided by University of Geneva



Background Spectrum at 300km and at an inclination of 42 deg. (without SAA)

Some estimations

- Different sims scenarios for POLAR-2 with p
 - Dose from p < 2 Gy for 2 yrs. mission (without SAA)
- n flux generally higher than p
- Neutrons easily penetrate shielding for charged particles and photons
 - n well absorbed in materials with Hydrogen
 - not considered in Sims scenarios
- Low n-Si interaction probability but produce additional damage than p (direct+indirect)
- Starting point for irradiation campaign:
 - **< 4.9x10¹¹ n on SiPM (2MeV)**
for 0.984 Gy/yr (extrapolation from p)

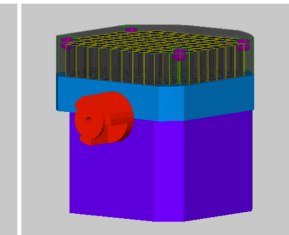
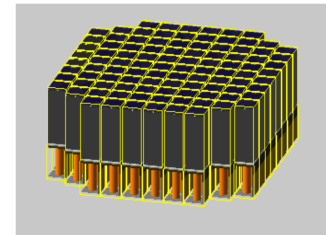
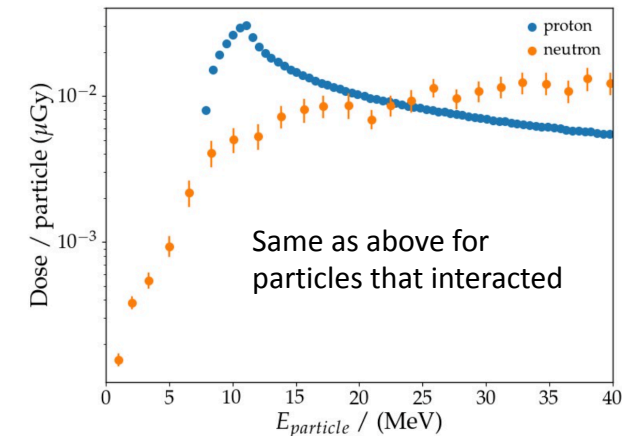
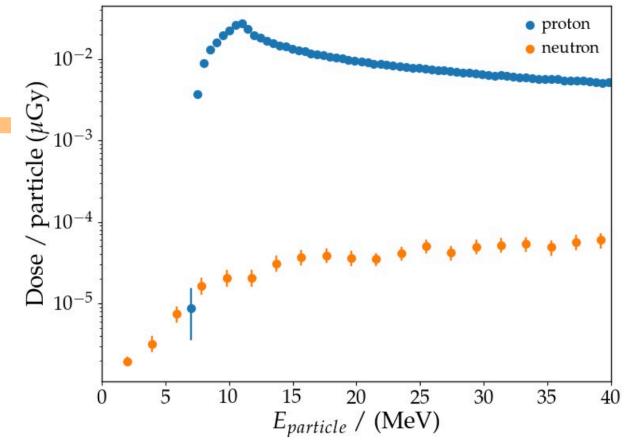
- from proton flux
- 100keV to 400MeV
- prediction for 2025
- solar maximum
- AP-8 model

Simulation Setup	POLAR-2 orbit
Bare Instrument	0.984 Gy/yr
Bare Instrument + SpaceLab	0.627 Gy/yr
Full Instrument	0.077 Gy/yr
Full Instrument + SpaceLab	0.064 Gy/yr

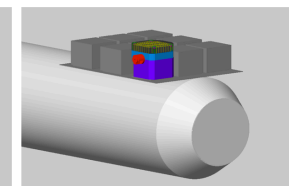
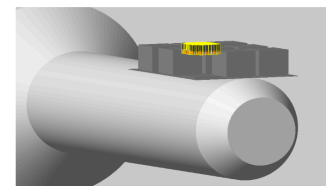
Bare instrument:
instrument component suspended in space. No further shielding.

Bare instrument + SpaceLab: same as top (left) figure but with the addition of the SpaceLab

Average p/n dose in Silicone

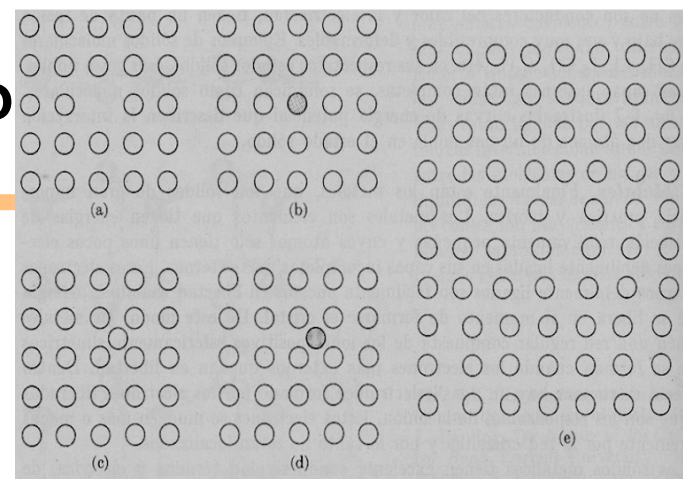


full instrument:
all instrument components suspended in space

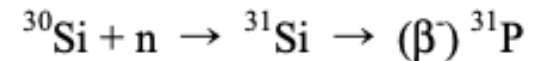
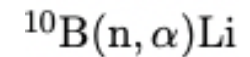
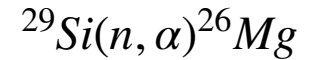


full instrument + SpaceLab: same as top (right) figure but with the addition of the SpaceLab

What do neutrons do to SiPM?



- Bulk damage in the crystalline structure
 - Increases SiPM noise: DarkCurrent, DCR, AP
 - May produce false triggering of detector
 - Bulk damage can also be from low energy n through indirect processes
- Surface damage of SiPM
 - Mostly from photons and low energy charged particles
 - Increases DarkCurrent & Power Consumption (important for space applications)
- Change of effective doping density
 - Low energy n produce transmutation doping in Si $^{30}\text{Si} + n \rightarrow ^{31}\text{Si} \rightarrow (\beta^-) ^{31}\text{P}$
 - Fast n produce Al/Mg (but 2 orders of magnitude less likely)
 - Removal of some dopants
- Other problems
 - Very difficult to shield
 - Activation
 - Additional impurities through other processes



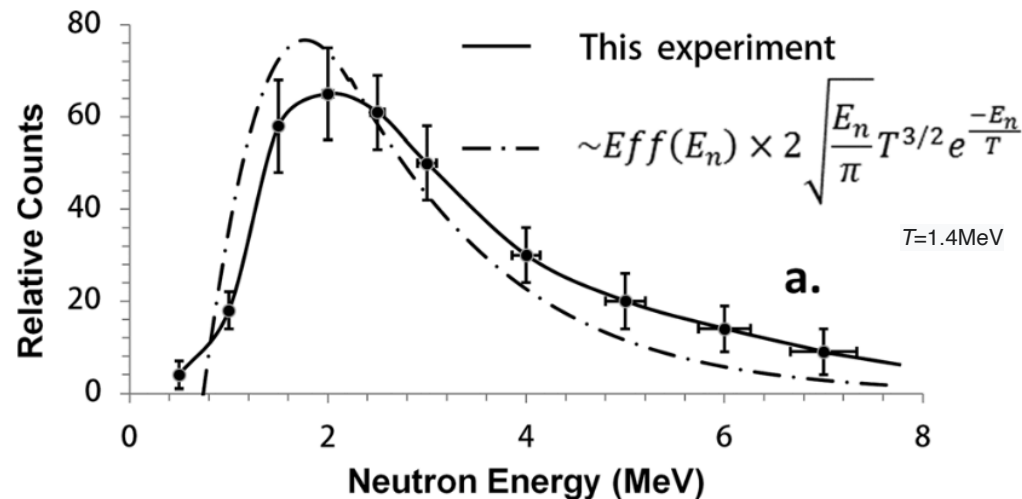
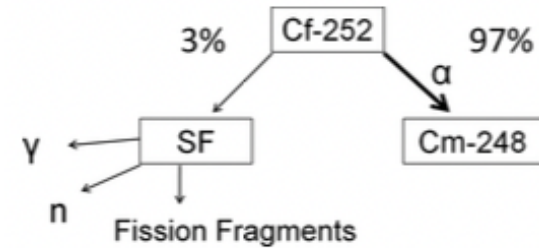
NIST Californium Neutron Irradiation Facility (CNIF)

- Located at NIST, Gaithersburg (Maryland, USA)
- Double room underground facility
 - Room with source in sub-room with n absorbers
 - Room for experiment preparation and remote control
- Cf-252 source intensity: $1.688 \times 10^7 \text{ ns}^{-1} (4\pi)$
 - At the moment of irradiation
 - Diameter $\sim 7.7\text{mm}$



Californium-252

- Neutrons and gammas from spontaneous fissions
 - Neutrons in the MeV order of magnitude
 - Expected bulk damage in Si lattice of the SiPM
 - Gammas rate $\sim 2n:1\gamma$ with $E < 155$ KeV
 - Expected some surface damage in the SiPM
- Alpha decay
 - Alphas stopped in ^{252}Cf source cladding (Pt-Ir capsule)



Experiment setup and strategy

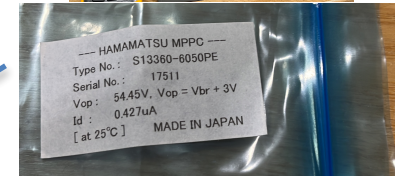
- 1 hr exposition @ 2.3 cm away from ^{252}Cf source center giving $\sim 3 \times 10^8$ n in the SiPM
 - $\sim 1000\times$ lower dose from sims compared to p but still much damage expected
 - Several exposures with different exposition time (check T)
- Measurements of dark-current after each exposure
 - In dark-box
 - Directly powered with a SMU Keithley 2450



Exposures and Dark-current

Date of 3 exposure 29/Oct/2021
 DR measurements taken 20s
 after polarization
 SiPM surface 0.36cm²

	Duration & Temp. of irradiation [h:m @ °C]	Fluence [ncm ⁻²]	n on SiPM [n]	Estim. ratio n:γ	Dark current @ Temp. @ Voltage [μA @ V @ T]
Before	-	-	-	-	0.3168 @54.5 @22.4
Exposure 1	1:00 @20.9	9.04E+08	3.25E+08	2:1	85.9 @54.5 @22.9
Exposure 2	1:13 @19.8	1.1E+09	3.96E+08	2:1	184.3 @54.5 @22.4
Exposure 3	1:32 @19.9	1.39E+09	5E+08	2:1	302.9 @54.5 @21.0

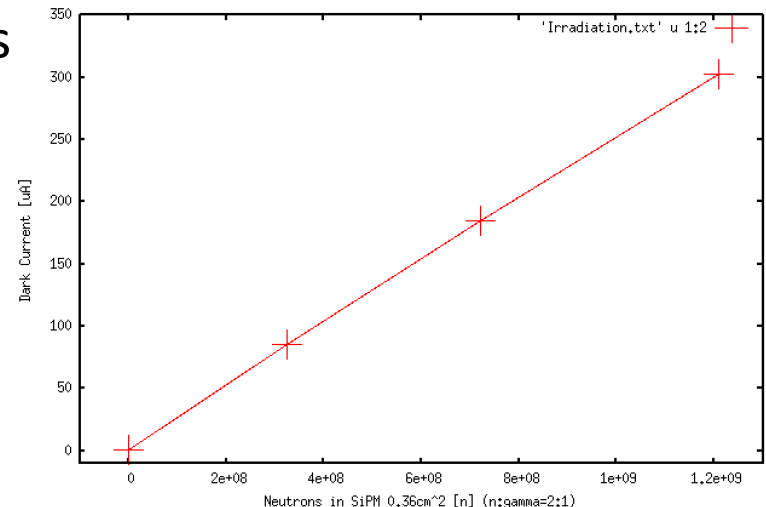


Dark-current before irradiation consistent with Hamamatsu

Almost 1000x Dark-current after 3 exposures

- x271 after 3.25x10⁸ n in the SiPM
- x581 after 7.21x10⁸ n
- x956 after 1.22x10⁹ n

SiPM S13360-6050PE Irradiation with Cf-252

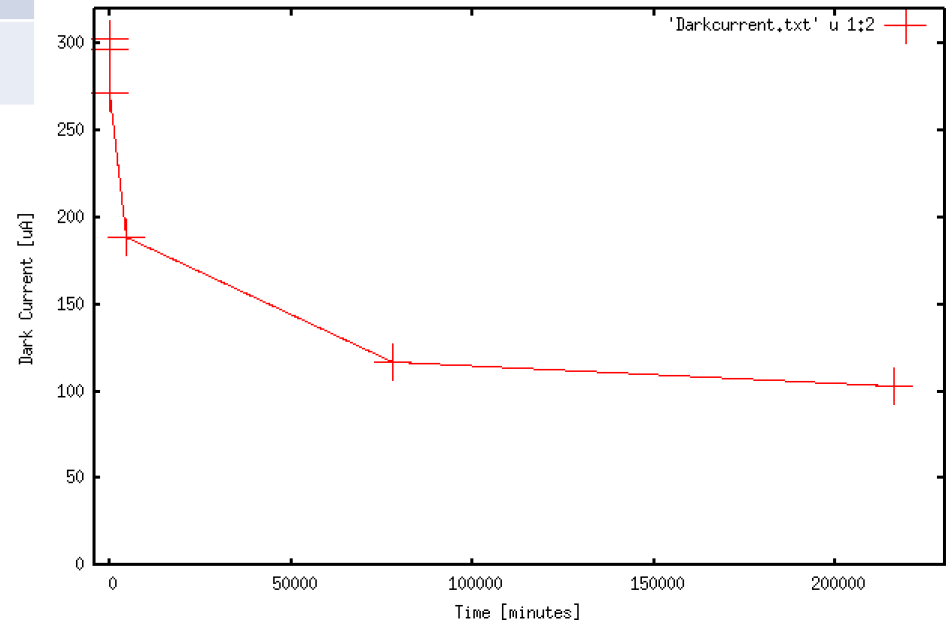


Dark-current settling

	Time after last irradi. [d h:m]	Dark current @ Temp. @ Voltage [μA @ V @ T]
Meas. 1	0d 00:00	302.9 @54.5 @22.4
Meas. 2	0d 00:03	297 @54.5 @22.7
Meas. 3	0d 00:36	272 @54.5 @23.3
Meas. 4	3d	189 @54.5 @20.6
Meas. 5	54d	117 @54.5 @24.0
Meas. 6	150d	103 @54.5 @24.0



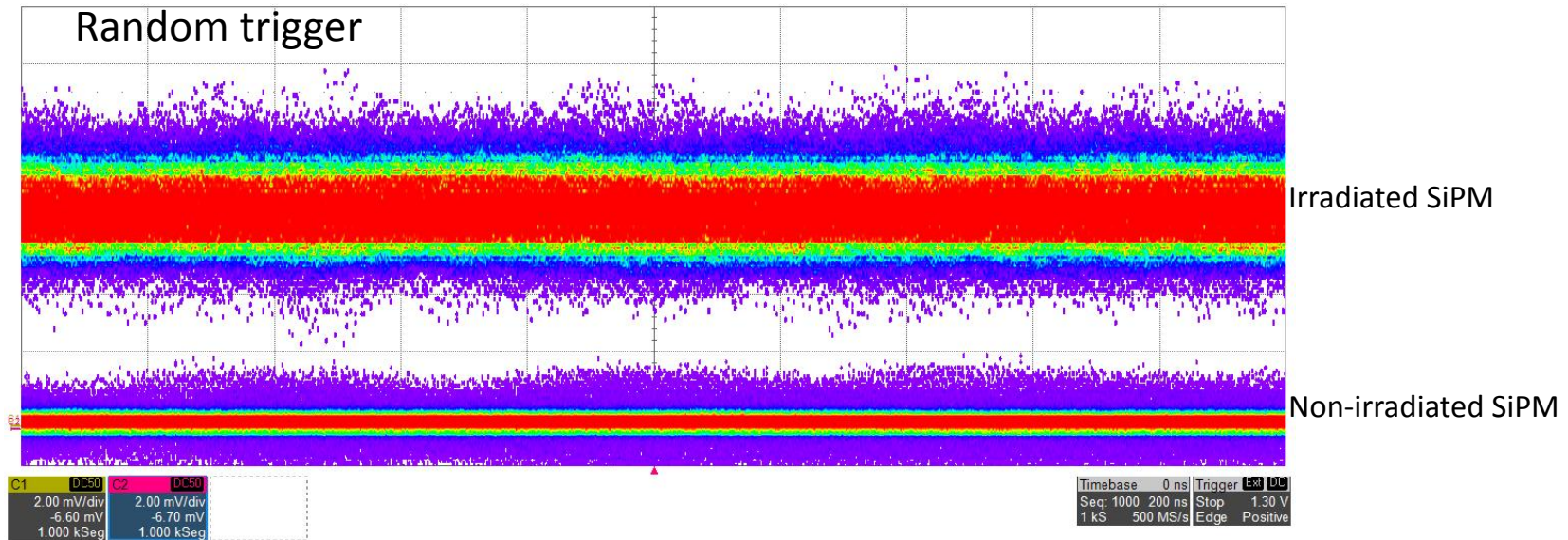
SiPM S13360-6050PE after 1.22×10^9 n from Cf-252



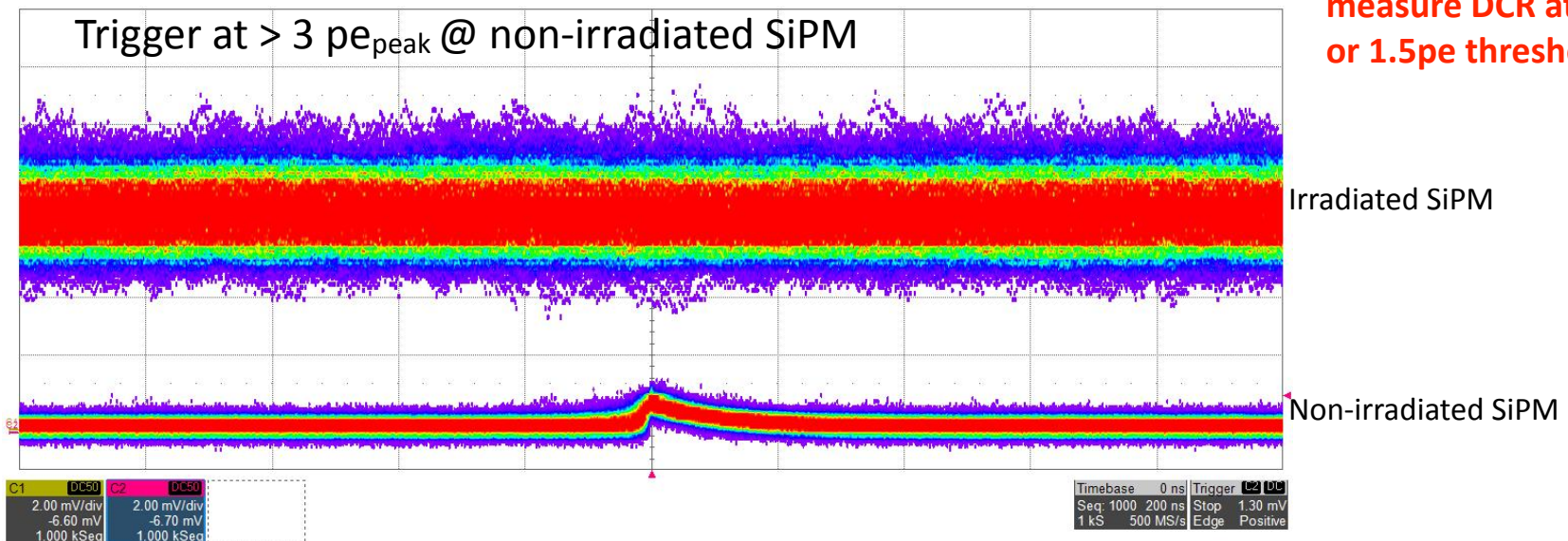
Result after slow annealing at room temperature

- 150 days storage @ $T \leq 25^\circ\text{C}$
- Total of 335x more than before irradiation

Baseline and Dark-pulses (@ 25°C)

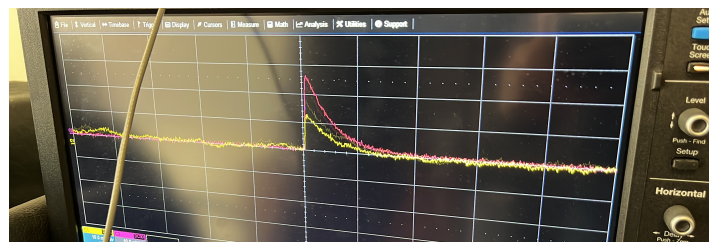
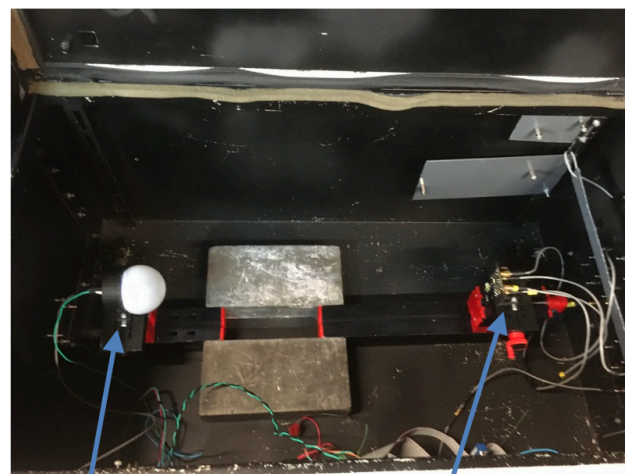
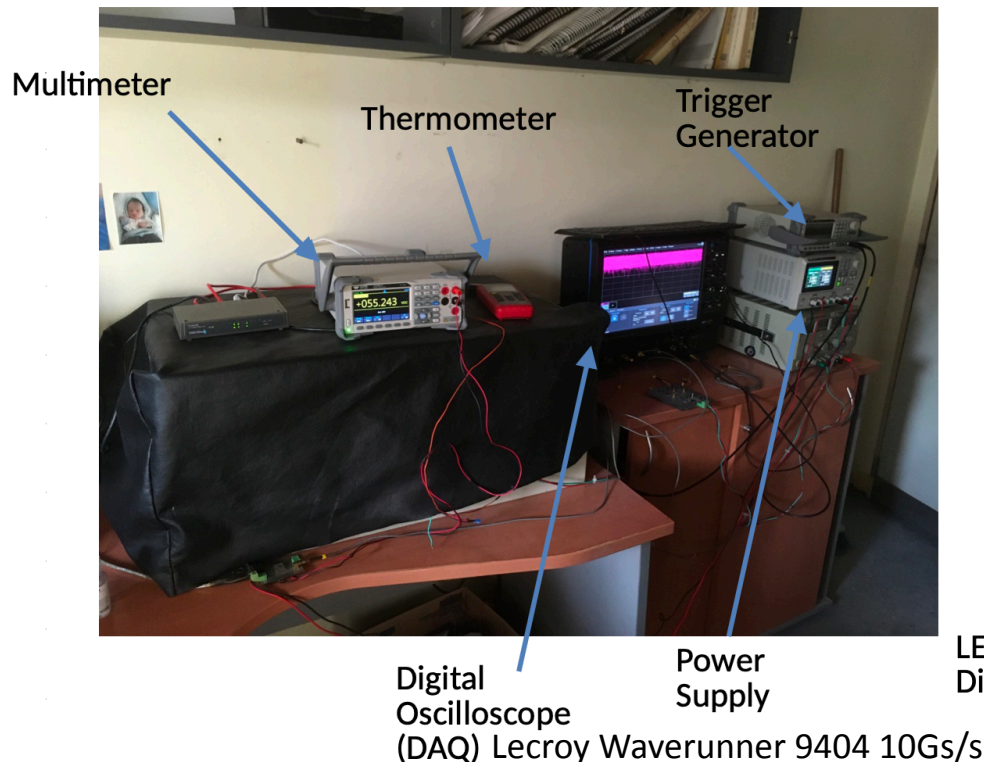


Not even possible to measure DCR at 0.5pe or 1.5pe threshold



Measurements with pulsed light

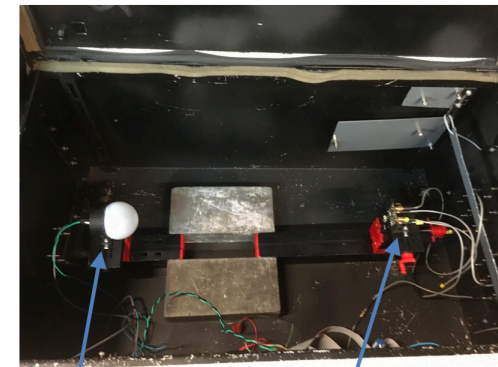
SiPM testing Setup at CNEA



- And it still works!!!!
 - at least with many pe
- But how well does it work?

Spectrums

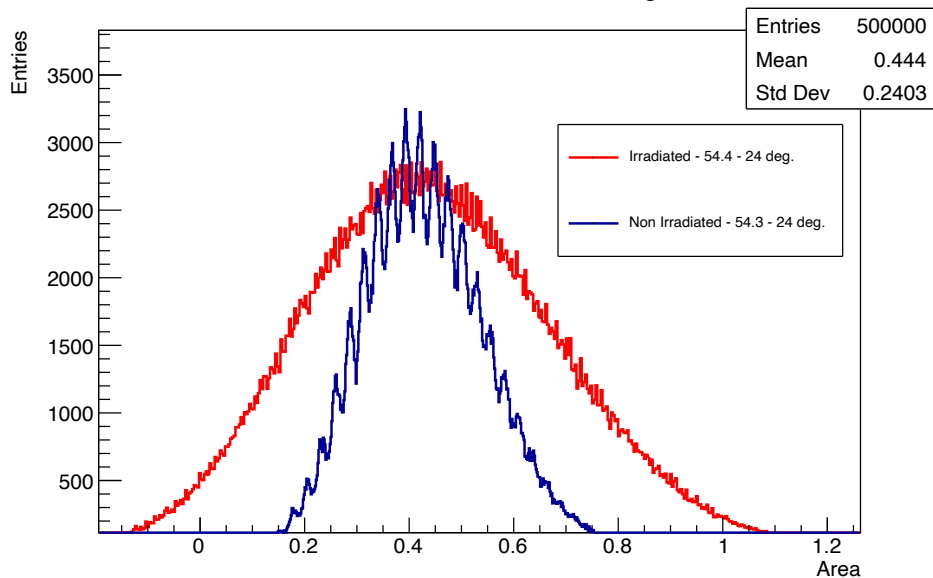
- Absolute calibration of Irradiated SiPM not possible with spectrums
 - Not even with 500000 million shots neither amplification
 - ENC too high
 - Artifacts in data analysis too high due to high DCR (poor S/N ratio) but it can be improved
- Cross-calibrated with non-irradiated SiPM with approx. same #photons



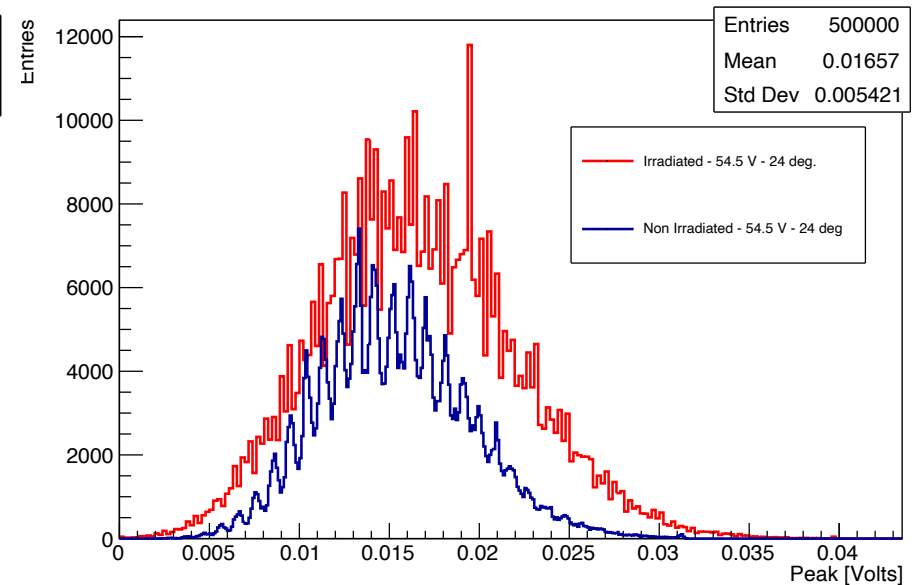
LED Driver + Diffuser

2 X S13360-6050PE (Irradiated Non Irradiated)

Irradiated - 54.4 - 24 deg.



Irradiated - 54.5 V - 24 deg.

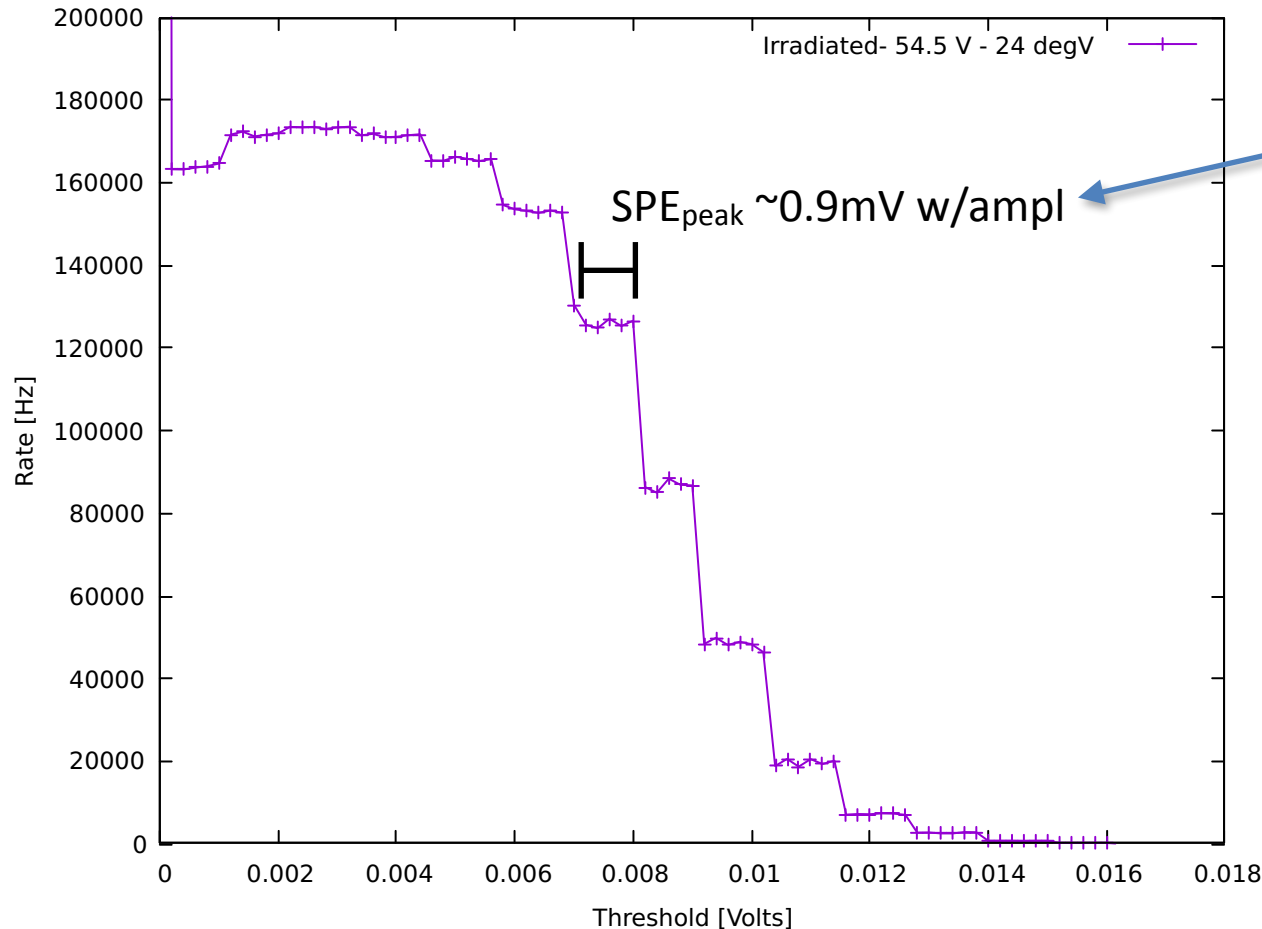


Charge and Peak spectrums for ~16pe @24°C with 5x amplifier calibrated with VNA

Peak spectrum for irradiated SiPM biased because artifacts in analysis due to big baseline fluctuations 12

Is it still useful to produce data & science?

- Still possible to roughly calibrate it through DCR vs. Threshold!?!



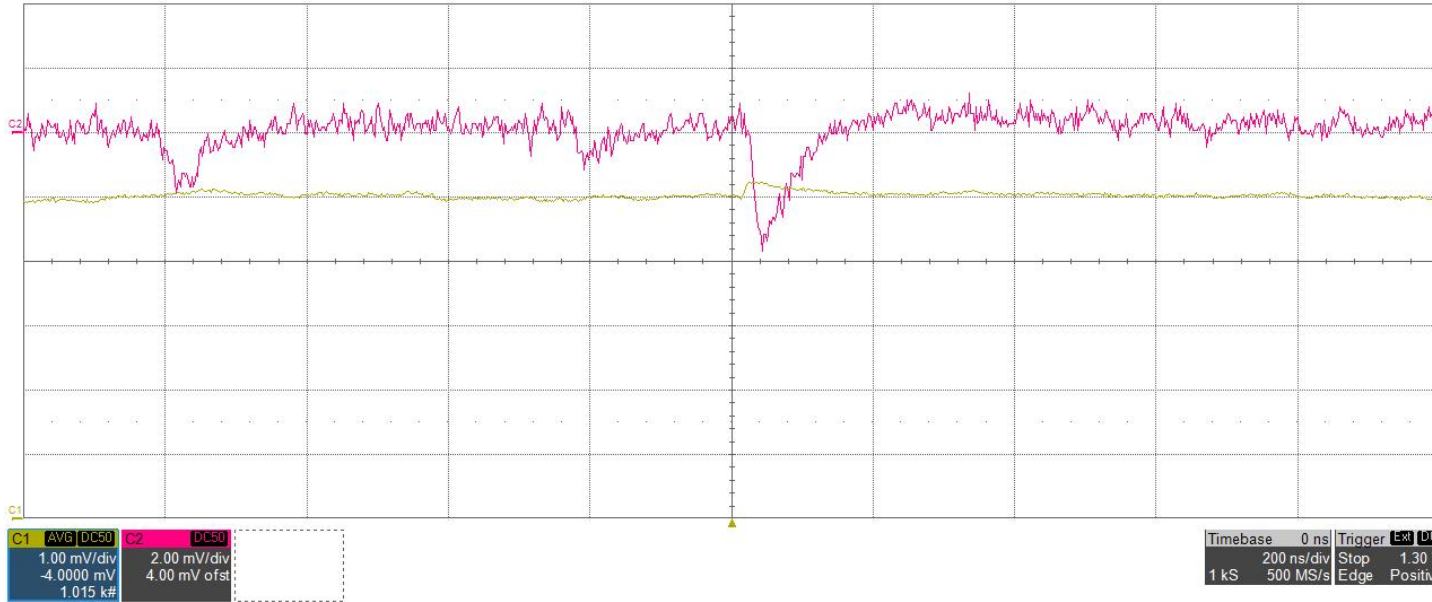
Consistent with spectrum from non-irradiated SiPM?!

Still to be debugged

- Absolutely useful for signals over 14pe
- Also shows accidental T1 self-trigger rate for lower thresholds

Is it still useful to produce data & science?

- Low #photos and T2s or External triggering
 - Possible through less damaged SiPMs and/or Event analysis



Non-irradiated amplified

Non-irradiated not amplified averaged

- Useful above ###photons with external triggering???
- but much lower than self-trigger

Conclusions:

- Results for Dark-current
 - $\sim 1000x$ increase in Dark-current after 3.394×10^9 n cm⁻² on SiPM area (from ²⁵²Cf and its γ)
 - Dark-current increases linearly with fluence in our exposition
 - Dark-current settles to $\sim 330x$ after 3 months at room temp.
- SiPM still works and detect pulsed light!!! but S/N ratio degrades at room temp.
 - Still useful for science by increasing threshold or advanced triggering
 - It can still be calibrated?!
 - May reduce acceptance of detector
- Next steps?
 - Measure other parameters: AP, CT, others???
 - Specification of SiPM “damage” for application?
 - Testing at application temperature?
 - Quantification of “damage” per Gy or Fluence for n vs. p at same E ?
 - Study effect of thermal neutrons in the SiPM?
 - thermal neutrons are very abundant in space

Muchas Gracias